

MONOLITHIC DUAL H BRIDGE DRIVER CIRCUIT

DESCRIPTION

NEC

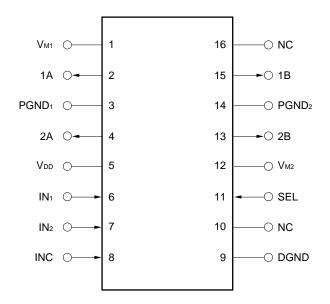
The μ PD16813 is a monolithic dual H bridge driver circuit which uses power MOS FETs in its driver stage. By complementing the P channel and N channel of the output stage, the circuit current has been substantially inproved as compared with that of conventional charge pump drivers.

The μ PD16813 is therefore ideal as the driver circuit of the 2-phase excitation, bipolar-driven stepping motor for the head actuator of an FDD.

FEATURES

- Low ON resistance (sum of ON resistors of top and bottom transistors) Ron = 2.0 Ω TYP.
- Low current consumption: $IDD = 100 \ \mu A MAX$.
- · Noise reduction circuit that operates when INC is OFF.
- · Compact surface mount package: 16-pin plastic SOP (300 mil)

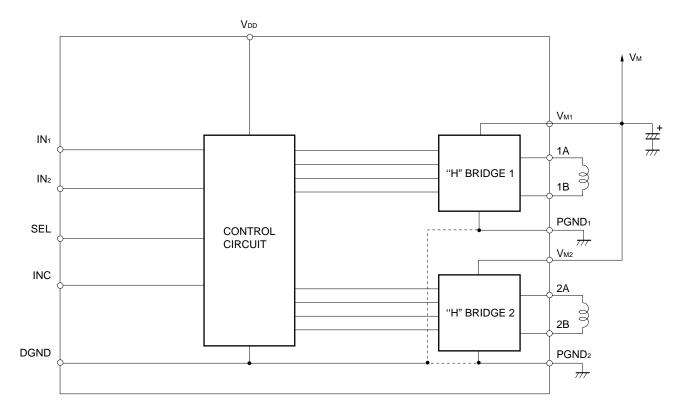
PIN CONFIGURATION (Top View)



ORDERING INFORMATION

Part Number	Package
μPD16813GS	16-pin plastic SOP (300 mil)

BLOCK DIAGRAM



FUNCTION TABLE

• In stop mode (SEL = High)

Excitation Direction	INC	IN1	IN ₂	H1	H2
<1>	Н	н	н	F	F
<2>	н	L	н	R	F
<3>	н	L	L	R	R
<4>	н	н	L	F	R
_	L	×	×	Stop	

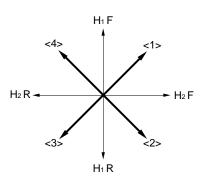
• In brake mode (SEL = Low)

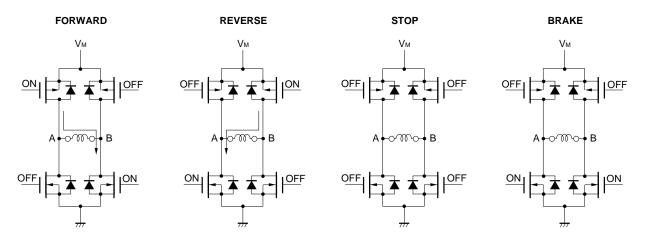
Excitation Direction	INC	IN1	IN2	H₁	H2
<1>	Н	н	н	F	F
<2>	Н	L	н	R	F
<3>	Н	L	L	R	R
<4>	Н	н	L	F R	
-	L	×	×	Bra	ake

F: Forward

R: Reverse

 \times : Don't care



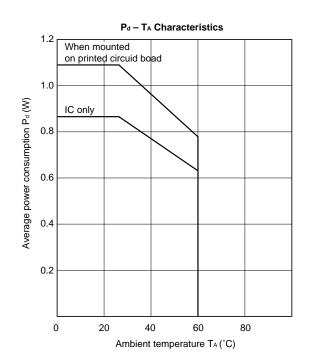


ABSOLUTE MAXIMUM RATINGS (T_A = +25 $^{\circ}$ C)

Parameter	Symbol	Rating	Unit
Supply voltage (motor block)	VM	-0.5 to +7	V
Supply voltage (control block)	Vdd	-0.5 to +7	V
Power consumption	Pd1	0.862 ^{Note 1}	W
	Pd2	1.087 ^{Note 2}	
Instantaneous H bridge driver current	I⊳ (pulse)	±1.0 ^{Note 2, 3}	A
Input voltage	Vin	−0.5 to V _{DD} + 0.5	V
Operating temperature range	TA	0 to 60	°C
Operation junction temperature	Tj MAX.	150	°C
Storage temperature range	Tstg	-55 to +125	°C

Notes 1. IC only

- 2. When mounted on a printed circuit board ($100 \times 100 \times 1$ mm, glass epoxy)
- **3.** $t \le 5$ ms, Duty ≤ 40 %



RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Supply voltage (motor block)	Vм	4.0	5.0	6.0	V
Supply voltage (control block)	Vdd	4.0	5.0	6.0	V
H bridge driver current ^{Note}	ldr			±310	mA
Operating temperature	TA	0		60	°C

Note When mounted on a printed circuit board ($100 \times 100 \times 1$ mm, glass epoxy)

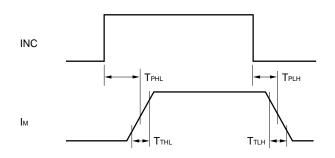
ELECTRICAL SPECIFICATIONS (Within recommended operating conditions unless otherwise specified)

Parameters	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
OFF V _M pin current	Ім	VM = 6.0 V, VDD = 6.0 V			1.0	μA
VDD pin current	loo				0.1	mA
Control pin high-level input current	Ін	Vin = Vdd			1.0	μA
Control pin low-level input current	lı∟	VIN = 0 V			-1.0	μA
Control pin high-level input voltage	Vін		3.0		Vdd + 0.3	V
Control pin low-level input voltage	VIL		-0.3		0.8	V
H bridge circuit ON resistance ^{Note 1}	Ron1	Vm = 5 V, Vdd = 5 V		2.0	4.0	Ω
Ron relative accuracy	ΔRon	Excitation direction <2>, <4>Note 2			±5	%
	ΔRon	Excitation direction <1>, <3>			±10	
H bridge circuit propagation delay time	tрнL	$V_{M} = 5 \text{ V}, \text{ V}_{DD} = 5 \text{ V}, \text{Note 3}$ $T_{A} = 25 \text{ °C}, \text{ R}_{M} = 20 \Omega$		2.0	2.5	μs
H bridge circuit propagation delay time	tрін			0.4	0.65	μs
H bridge circuit rise time	tтнL	$V_M = 5 \text{ V}, \text{ V}_{DD} = 5 \text{ V}, \text{Note } 3$		0.2	0.4	μs
H bridge circuit fall time	tтLH	T _A = 25 °C, R _M = 20 Ω		0.1	0.2	μs

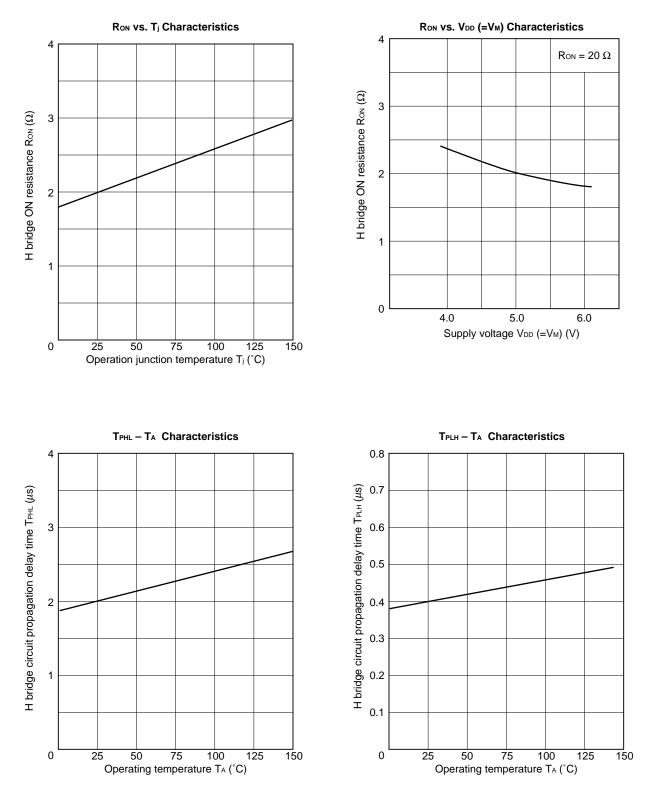
Notes 1. Sum of ON resistances of top and bottom transistors

2. For the excitation direction, refer to FUNCTION TABLE.

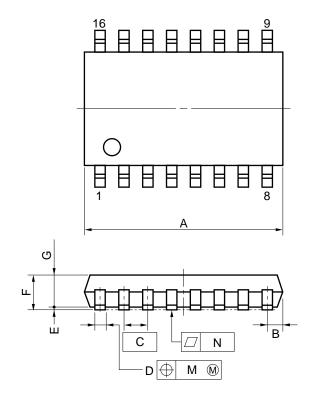
3.



CHARACTERISTIC CURVES

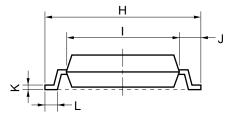


16 PIN PLASTIC SOP (300 mil)



detail of lead end





NOTE

Each lead centerline is located within 0.12 mm (0.005 inch) of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS	INCHES
А	10.46 MAX.	0.412 MAX.
В	0.78 MAX.	0.031 MAX.
С	1.27 (T.P.)	0.050 (T.P.)
D	$0.40^{+0.10}_{-0.05}$	$0.016^{+0.004}_{-0.003}$
Е	0.1±0.1	0.004±0.004
F	1.8 MAX.	0.071 MAX.
G	1.55	0.061
Н	7.7±0.3	0.303±0.012
I	5.6	0.220
J	1.1	0.043
К	$0.20^{+0.10}_{-0.05}$	$0.008^{+0.004}_{-0.002}$
L	0.6±0.2	$0.024^{+0.008}_{-0.009}$
М	0.12	0.005
Ν	0.10	0.004
Р	3°+7° -3°	3°+7° -3°
		P16GM-50-300B-

RECOMMENDED SOLDERING CONDITIONS

It is recommended to solder this product under the conditions described below. For soldering methods and conditions other than those listed below, consult NEC.

Surface mount type

For the details of the recommended soldering conditions of this type, refer to **Semiconductor Device Mounting Technology Manual (C10535E)**.

Soldering Method	Soldering Conditions	Symbol of Recommended Soldering	
Infrared reflow	Peak package temperature: 230 °C, Time: 30 seconds MAX. (210 °C MIN.), Number of times: 1, Number of days: None ^{Note}	IR30-00	
VPS	Peak package temperature: 215 °C, Time: 40 seconds MAX. (200 °C MIN.), Number of times: 1, Number of days: None ^{Note}	VP15-00	
Wave soldering	Solder bath temperature: 260 °C MAX., Time: 10 seconds MAX., Number of times: 1, Number of days: None ^{Note}	WS60-00	
Partial heating	Pin temperature: 300 °C MAX., Time: 10 seconds MAX., Number of days: None ^{Note}	-	

Note The number of storage days at 25 °C, 65 % RH after the dry pack has been opened

Caution Do not use two or more soldering methods in combination (except partial heating).

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Anti-radioactive design is not implemented in this product.

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